

What is claimed is:

1. A symmetrical stacked inductor comprising:

a plurality of conductive layers comprising at least one conductive line formed out of a symmetrical and geometric conductive layer and comprising at least one inter-metal dielectric layer for isolating each conductive layer, and wherein the conductive line does not intersect; and

a plurality of vias placing between the inter-metal dielectric layers for electrical conduction.

2. The symmetrical stacked inductor of claim 1, wherein the geometric conductive layer is rectangular.

3. The symmetrical stacked inductor of claim 1, wherein the geometric conductive layer is a circular.

4. The symmetrical stacked inductor of claim 1, further comprising a tapped apparatus between the symmetrical stacked inductors.

5. The symmetrical stacked inductor of claim 1, wherein two symmetrical stacked inductors are used to form a single chip transformer.

6. The symmetrical stacked inductor of claim 1, wherein two symmetrical stacked inductors are used to form a single chip balun element.

7. The symmetrical stacked inductor of claim 1, wherein the conductive line is selected from aluminum, copper, aluminum-copper alloy, and any conductive metal.

8. The symmetrical stacked inductor of claim 1, wherein the size of the symmetrical and geometric even conductive layer is not the same as the size of the symmetrical and geometric odd conductive layer.

9. The symmetrical stacked inductor of claim 8, wherein the inside of the even conductive layer has an inside even conductive layer being the same

as the symmetrical and geometric odd conductive layer and being parallel with the odd conductive layer, wherein the even conductive layer does not intersect with the inside even conductive layer, and wherein the inside even conductive layer is connected to the odd conductive layer by the vias and between them is the inter-metal dielectric layer.

10. The symmetrical stacked inductor of claim 9, wherein the outside of the odd conductive layer has an outside odd conductive layer being the same as the even conductive layer and being parallel with the odd conductive layer, wherein the outside odd conductive layer does not intersect with the odd conductive layer, and wherein the outside odd conductive layer is connected to the even conductive layer by the vias and between them is the inter-metal dielectric layer.

11. The symmetrical stacked inductor of claim 1, wherein the conductive layer comprises two conductive lines.